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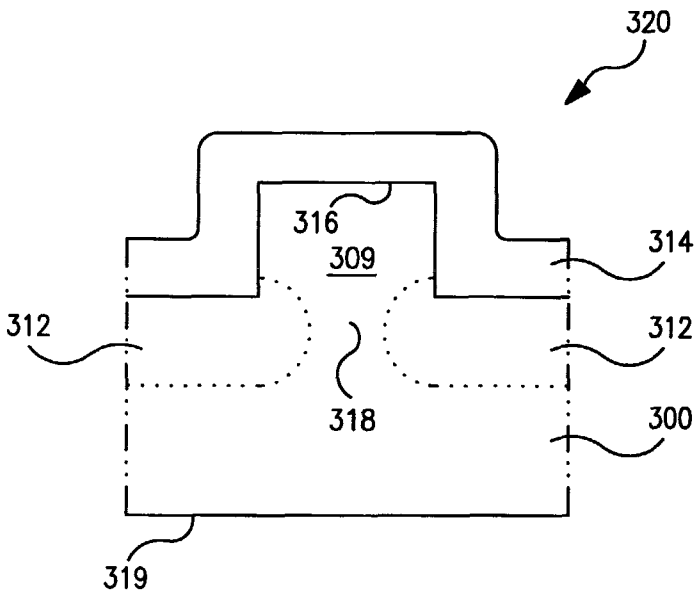
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(54) Title: VERTICAL JUNCTION FIELD EFFECT SEMICONDUCTOR DIODES



(57) Abstract: Semiconductor diodes (320) ae diode connected vertical cylindrical field effect devices having one diode terminal (314) as the common connection between a gate (312) and a source/drain (309) of the vertical cylindrical field effect devices. Methods of forming the diode connected vertical cylindrical field effect devices are disclosed.

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